

Surface Mount Schottky Barrier Rectifier

Features

- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- Case: SMAF



Top View
 Marking Code: SS32
 Simplified outline SMAF and symbol

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

Absolute Maximum Ratings and Electrical characteristics

Parameter	Symbols	SS32F	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	20	V
Maximum RMS voltage	V_{RMS}	14	V
Maximum DC Blocking Voltage	V_{DC}	20	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	3.0	A
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	80	A
Max Instantaneous Forward Voltage at 3 A	V_F	0.55	V
Maximum DC Reverse Current $T_a = 25^\circ\text{C}$ at Rated DC Reverse Voltage $T_a = 100^\circ\text{C}$	I_R	0.5 5	mA
Typical Junction Capacitance ⁽¹⁾	C_j	250	pF
Typical Thermal Resistance ⁽²⁾	$R_{\theta JA}$ $R_{\theta JC}$	70 18	$^\circ\text{C/W}$
Operating Junction Temperature Range	T_j	-55 ~ +150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 ~ +150	$^\circ\text{C}$

(1) Measured at 1 MHz and applied reverse voltage of 4 V D.C

(2) P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

Fig.1 Forward Current Derating Curve

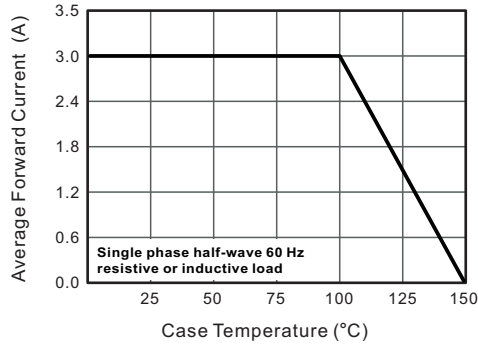


Fig.2 Typical Reverse Characteristics

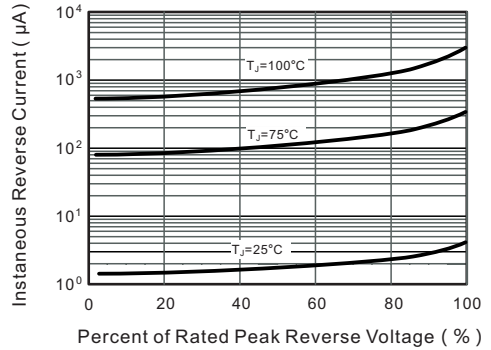


Fig.3 Typical Forward Characteristic

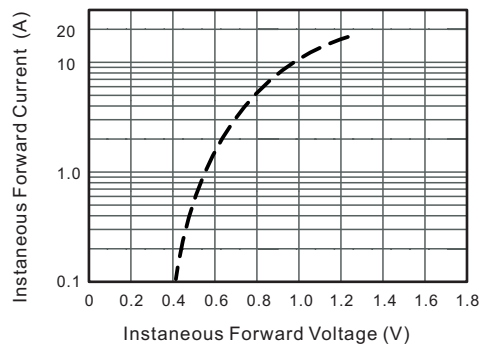


Fig.4 Typical Junction Capacitance

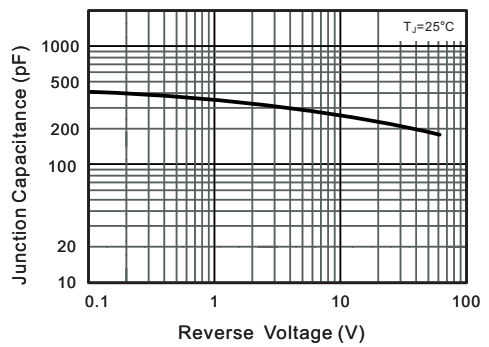


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

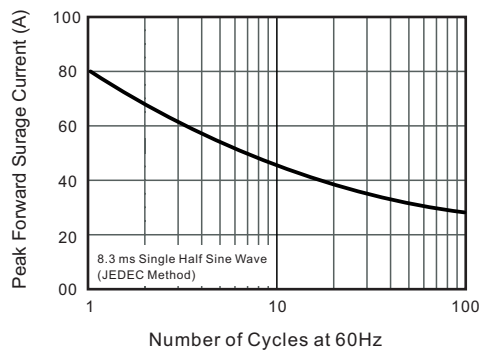


Fig.5- Typical Transient Thermal Impedance

